

# Silizium-Fotodiode

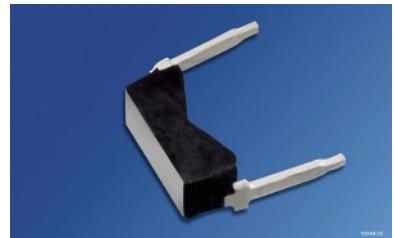
## Silicon Photodiode

BPX 90

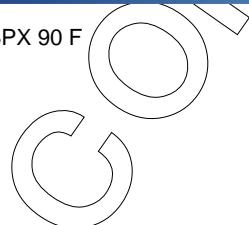
BPX 90 F



BPX 90



BPX 90 F



### Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm (BPX 90) und bei 950 nm (BPX 90 F)
- Hohe Fotoempfindlichkeit
- DIL-Plastikbauförm mit hoher Packungsdichte

### Anwendungen

- Industrieelektronik
- „Messen/Steuern/Regeln“

| Typ<br>Type | Bestellnummer<br>Ordering Code |
|-------------|--------------------------------|
| BPX 90      | Q62702-P47                     |
| BPX 90 F    | Q62702-P928                    |

### Features

- Especially suitable for applications from 400 nm to 1100 nm (BPX 90) and of 950 nm (BPX 90 F)
- High photosensitivity
- DIL plastic package with high packing density

### Applications

- Industrial electronics
- For control and drive circuits

**Grenzwerte****Maximum Ratings**

| Bezeichnung<br>Parameter  | Symbol<br>Symbol  | Wert<br>Value | Einheit<br>Unit |
|---|-------------------|---------------|-----------------|
| Betriebs- und Lagertemperatur<br>Operating and storage temperature range  | $T_{op}; T_{stg}$ | - 40 ... + 80 | °C              |
| Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s)<br>Soldering temperature in 2 mm distance from case bottom ( $t \leq 3$ s) | $T_s$             | 230           | °C              |
| Sperrspannung<br>Reverse voltage  | $V_R$             | 32            | V               |
| Verlustleistung, $T_A = 25$ °C<br>Total power dissipation   | $P_{tot}$         | 100           | mW              |

**Kennwerte  $T_A = 25$  °C****Characteristics**

| Bezeichnung<br>Parameter   | Symbol<br>Symbol             | Wert<br>Value    |                  | Einheit<br>Unit |
|--|------------------------------|------------------|------------------|-----------------|
|  |                              | BPX 90           | BPX 90 F         |                 |
| Fotostrom<br>Photocurrent  | $I_P$                        | 45 ( $\geq 32$ ) | -                | µA              |
| $V_R = 5$ V, Normlicht/standard light A,<br>$T = 2856$ K, $E_V = 1000$ lx              | $I_P$                        | -                | 26 ( $\geq 16$ ) | µA              |
| $V_R = 5$ V, $\lambda = 950$ nm, $E_e = 1$ mW/cm <sup>2</sup>                          | $\lambda_{S \max}$           | 830              | 950              | nm              |
| Wellenlänge der max. Fotoempfindlichkeit<br>Wavelength of max. sensitivity             |                              |                  |                  |                 |
| Spektraler Bereich der Fotoempfindlichkeit<br>$S = 10\%$ von $S_{max}$                 | $\lambda$                    | 400 ... 1150     | 800 ... 1150     | nm              |
| Spectral range of sensitivity<br>$S = 10\%$ of $S_{max}$                               |                              |                  |                  |                 |
| Bestrahlungsempfindliche Fläche<br>Radiant sensitive area                              | A                            | 5.5              | 5.5              | mm <sup>2</sup> |
| Abmessung der bestrahlungsempfindlichen Fläche<br>Dimensions of radiant sensitive area | $L \times B$<br>$L \times W$ | 1.75 × 3.15      | 1.75 × 3.15      | mm × mm         |
| Abstand Chipoberfläche zu Gehäuseoberfläche<br>Distance chip front to case surface     | H                            | 0.5              | 0.5              | mm              |
| Halbwinkel<br>Half angle   | φ                            | ± 60             | ± 60             | Grad<br>deg.    |

Kennwerte  $T_A = 25^\circ\text{C}$ 

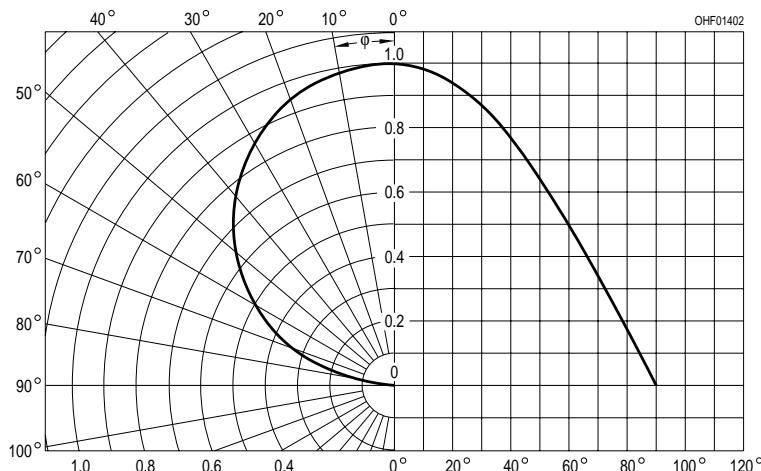
Characteristics (cont'd)

| Bezeichnung<br>Parameter  | Symbol<br>Symbol | Wert<br>Value      |                    | Einheit<br>Unit     |
|---|------------------|--------------------|--------------------|---------------------|
|   |                  | BPX 90             | BPX 90 F           |                     |
| Dunkelstrom, $V_R = 10 \text{ V}$<br>Dark current   | $I_R$            | 5 ( $\leq 180$ )   | 5 ( $\leq 180$ )   | nA                  |
| Spektrale Fotoempfindlichkeit, $\lambda = 950 \text{ nm}$<br>Spectral sensitivity   | $S_\lambda$      | 0.48               | 0.48               | A/W                 |
| Quantenausbeute, $\lambda = 950 \text{ nm}$<br>Quantum yield  | $\eta$           | 0.62               | 0.62               | Electrons<br>Photon |
| Leerlaufspannung<br>Open-circuit voltage<br>$E_v = 1000 \text{ lx}$ , Normlicht/standard light A,<br>$T = 2856 \text{ K}$<br>$E_e = 0.5 \text{ mW/cm}^2$ , $\lambda = 950 \text{ nm}$       | $V_O$            | 450 ( $\geq 380$ ) | —                  | mV                  |
|   | $V_O$            | —                  | 400 ( $\geq 340$ ) | mV                  |
| Kurzschlußstrom<br>Short-circuit current<br>$E_v = 1000 \text{ lx}$ , Normlicht/standard light A,<br>$T = 2856 \text{ K}$<br>$E_e = 0.5 \text{ mW/cm}^2$ , $\lambda = 950 \text{ nm}$       | $I_{SC}$         | —                  | 13                 | $\mu\text{A}$       |
| Anstiegs- und Abfallzeit des Fotostromes<br>Rise and fall time of the photocurrent<br>$R_L = 1 \text{ k}\Omega$ ; $V_R = 5 \text{ V}$ ; $\lambda = 850 \text{ nm}$ ; $I_p = 30 \mu\text{A}$ | $t_r, t_f$       | 1.3                | 1.3                | $\mu\text{s}$       |
| Durchlaßspannung, $I_F = 80 \text{ mA}$ , $E = 0$<br>Forward voltage  | $V_F$            | 1.3                | 1.3                | V                   |
| Kapazität, $V_R = 0 \text{ V}$ , $f = 1 \text{ MHz}$ , $E = 0$<br>Capacitance   | $C_0$            | 430                | 430                | pF                  |

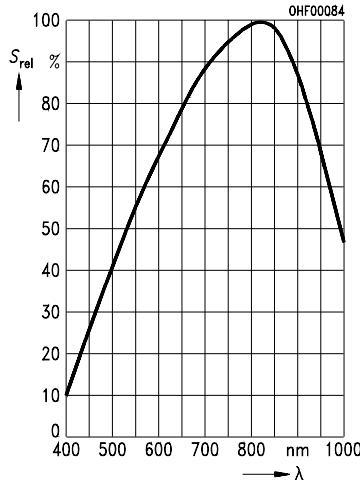
Kennwerte  $T_A = 25^\circ\text{C}$ 

Characteristics (cont'd)

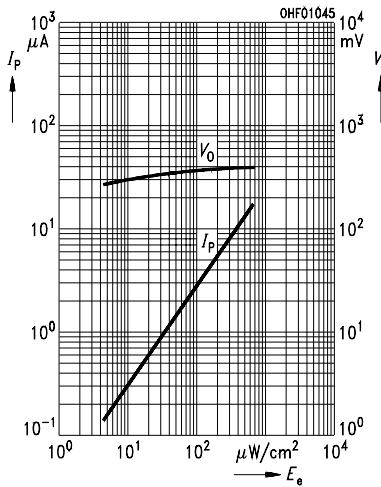
| Bezeichnung<br>Parameter   | Symbol<br>Symbol | Wert<br>Value        |                      | Einheit<br>Unit                                      |
|--|------------------|----------------------|----------------------|--|
|  |                  | BPX 90               | BPX 90 F             |  |
| Temperaturkoeffizient von $V_O$<br>Temperature coefficient of $V_O$  | $TC_V$           | - 2.6                | - 2.6                | mV/K   |
| Temperaturkoeffizient von $I_{SC}$<br>Temperature coefficient of $I_{SC}$  | $TC_I$           |                      |                      |  |
| Normlicht/standard light A   | $TC_I$           | 0.18                 | -                    | %/K  |
| $\lambda = 950 \text{ nm}$   | $TC_I$           | -                    | 0.2                  | %/K  |
| Rauschäquivalente Strahlungsleistung<br>Noise equivalent power<br>$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$ | $NEP$            | $8 \times 10^{-14}$  | $8 \times 10^{-14}$  | $\frac{\text{W}}{\sqrt{\text{Hz}}}$                  |
| Nachweisgrenze, $V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$<br>Detection limit                                | $D^*$            | $2.9 \times 10^{12}$ | $2.9 \times 10^{12}$ | $\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$ |

Directional Characteristics  $S_{\text{rel}} = f(\phi)$ 

**Relative Spectral Sensitivity**  
BPX 90  $S_{\text{rel}} = f(\lambda)$

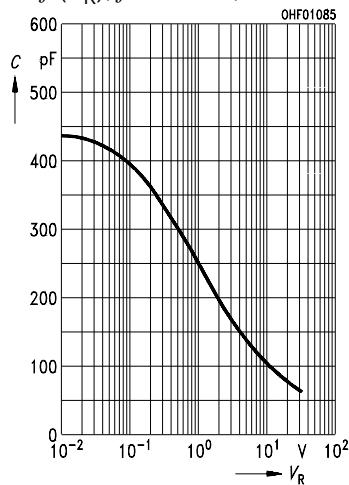


**Photocurrent  $I_P = f(E_e)$ ,  $V_R = 5 \text{ V}$**   
**Open-Circuit Voltage  $V_O = f(E_e)$**   
BPX 90 F

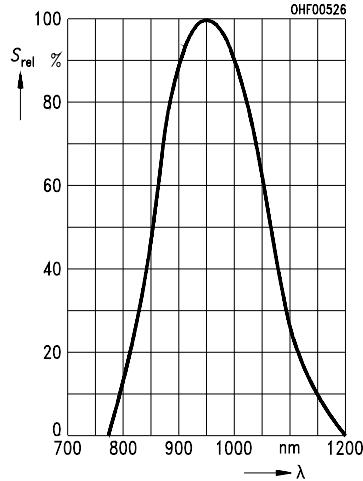


**Capacitance**

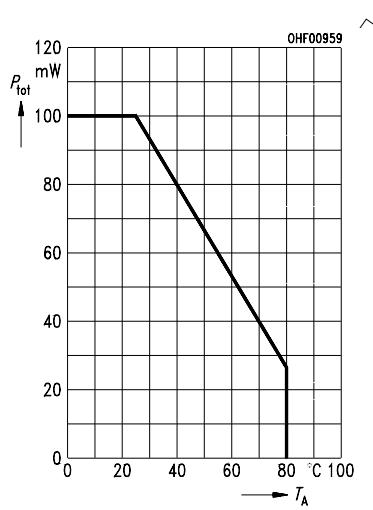
$C = f(V_R)$ ,  $f = 1 \text{ MHz}$ ,  $E = 0$



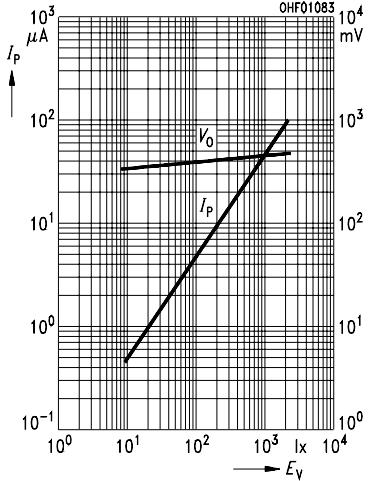
**Relative Spectral Sensitivity**  
BPX 90 F  $S_{\text{rel}} = f(\lambda)$



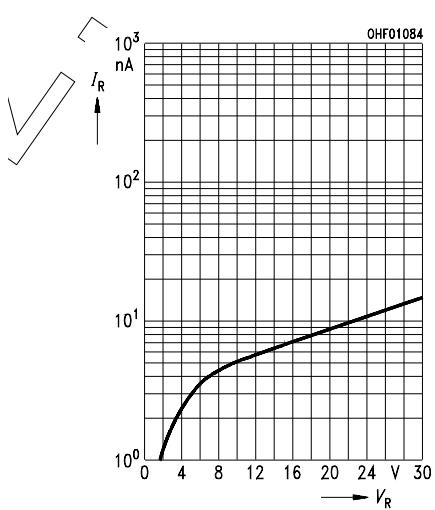
**Total Power Dissipation**  
 $P_{\text{tot}} = f(T_A)$



**Photocurrent  $I_P = f(E_V)$ ,  $V_R = 5 \text{ V}$**   
**Open-Circuit Volt. BPX 90  $V_O = f(E_V)$**

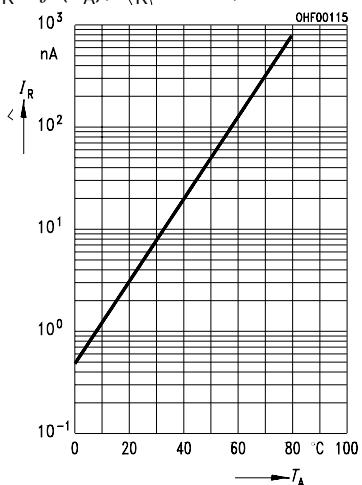


**Dark Current**  
 $I_R = f(V_R)$ ,  $E = 0$

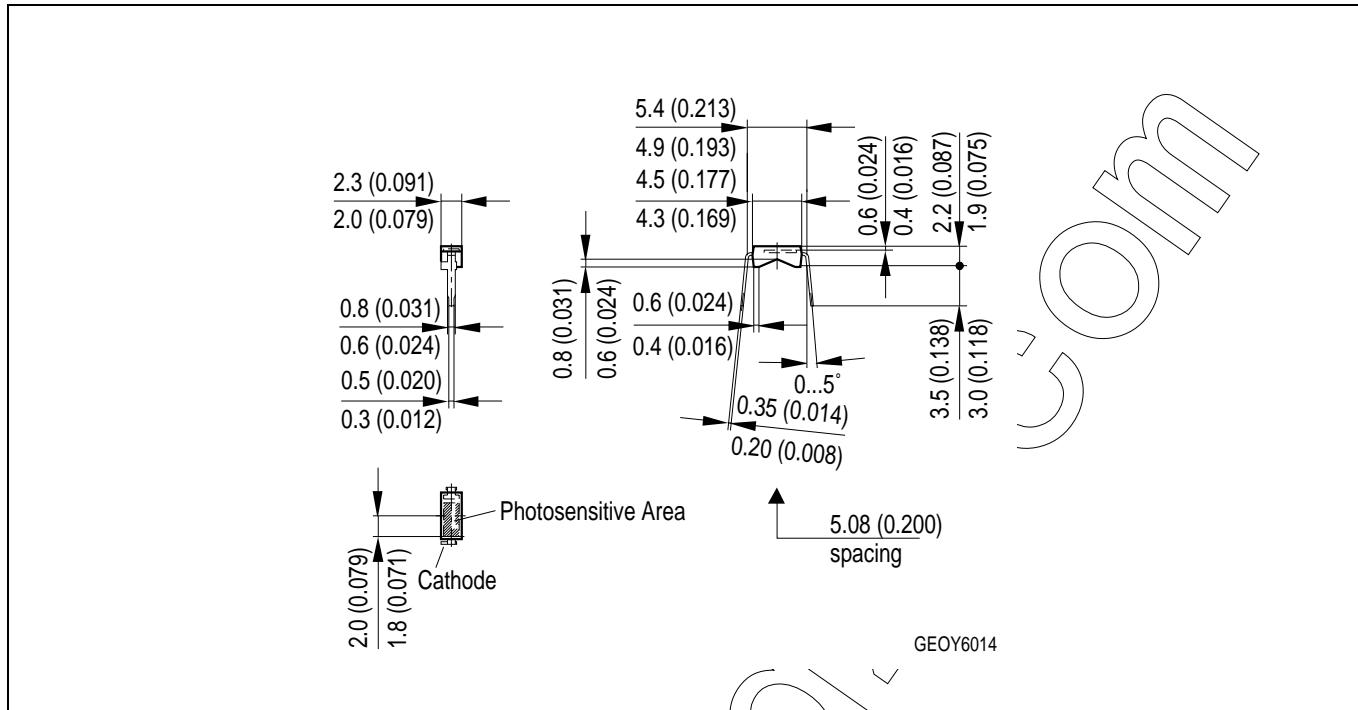


**Dark Current**

$I_R = f(T_A)$ ,  $V_R = 10 \text{ V}$ ,  $E = 0$



## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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### Attention please!

The information describes the type of component and shall not be considered as assured characteristics.  
Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

### Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

**Components used in life-support devices or systems must be expressly authorized for such purpose!** Critical components<sup>1</sup>, may only be used in life-support devices or systems<sup>2</sup> with the express written approval of OSRAM OS.

<sup>1</sup> A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

<sup>2</sup> Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.